

#### General Description

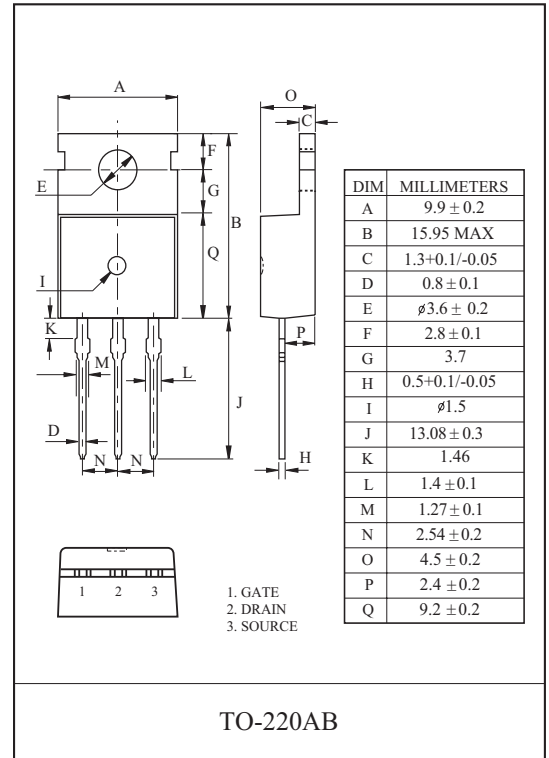
This planar stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for active power factor correction, electronic lamp ballasts based on half bridge topology and switching mode power supplies.

#### FEATURES

- $V_{DSS} = 60V$ ,  $I_D = 50A$
- Drain-Source ON Resistance :  
 $R_{DS(ON)} = 17m\ \Omega$  (Max.) @  $V_{GS} = 10V$
- $Qg$ (typ.) = 39.5nC

#### MOSFET MAXIMUM RATING (Ta=25 °C Unless otherwise noted)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$		



\* : Drain current limited by maximum junction temperature.